

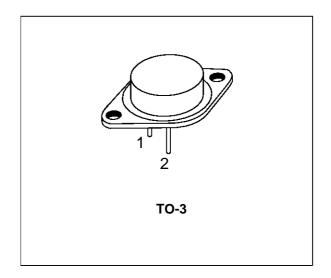


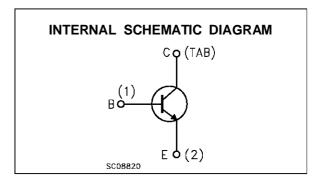
HIGH POWER NPN SILICON TRANSISTOR

- HIGH EFFICIENCY SWITCHING
- VERY LOW SATURATION VOLTAGE
- RECTANGULAR SAFE OPERATION AREA
- WIDE ACCIDENTAL OVERLOAD AREA

DESCRIPTION

Suitable for motor drivers, SMPS converters, uninterruptable power supply operating low voltage supply.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage (V _{BE} = -1.5V)	200	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	125	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
ΙE	Emitter Current	50	Α
ІЕМ	Emitter Peak Current	150	Α
Ι _Β	Base Current	10	Α
I _{BM}	Base Peak Current	30	Α
P _{tot}	Total Dissipation at T _c < 25 °C	300	W
T _{stg}	Storage Temperature	-65 to 200	°C
Tj	Max. Operating Junction Temperature	200	°C

October 1995 1/4

THERMAL DATA

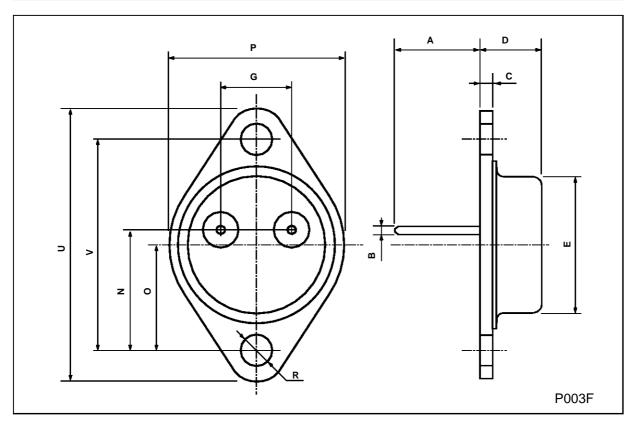
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CER}	Collector Cut-off Current ($R_{BE} = 5\Omega$)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ $T_{C} = 100^{\circ}C$			1 5	mA mA
I _{CEV}	Collector Cut-off Current	$V_{CE} = V_{CEV}$ $V_{BE} = -1.5V$ $V_{CE} = V_{CEV}$ $V_{BE} = -1.5V$ $TC = 100$ °C			1 4	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage	I _C = 0.2mA L = 25mH	125			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 50mA	7			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$\begin{array}{llllllllllllllllllllllllllllllllllll$			0.9 0.9 1.2 1.5	V V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	$\begin{array}{llllllllllllllllllllllllllllllllllll$			1.4 2 1.4 2.1	V V V
di _c /dt	Rate of Rise of on-state Collector Current	$VCC = 100V R_C = 0$ $I_{B1} = 5A$ $T_p = 3\mu s$ $T_j = 100^{\circ}C$	180			A/μs
ts t _f t _c	INDUCTIVE LOAD Storage time Fall Time Crossover Time	$\begin{array}{lll} V_{CC} = 90V & V_{clamp} = 125 \ V \\ I_{C} = 50A & I_{B1} = 2.5A \\ V_{BB} = -5V & L_{C} = 80 \mu H \\ R_{B2} = 1 \ \Omega & T_{j} = 100 \ ^{o}C \end{array}$			2 0.2 0.35	μs μs μs
V _{CEW}	Maximum Collector Emitter Voltage without Snubber	$\begin{array}{ll} V_{CC} = 90V & I_{CWoff = 150A} \\ v_{BB} = -5V & I_{B1} = 10A \\ L_{C} = 30\mu H & R_{B2} = 1\Omega \\ T_{j} = 125^{\circ}C \end{array}$	125			V

^{*} Pulsed: Pulse duration = 3μs, duty cycle = 2 %

TO-3 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	11.00		13.10	0.433		0.516	
В	0.97		1.15	0.038		0.045	
С	1.50		1.65	0.059		0.065	
D	8.32		8.92	0.327		0.351	
E	19.00		20.00	0.748		0.787	
G	10.70		11.10	0.421		0.437	
N	16.50		17.20	0.649		0.677	
Р	25.00		26.00	0.984		1.023	
R	4.00		4.09	0.157		0.161	
U	38.50		39.30	1.515		1.547	
V	30.00		30.30	1.187		1.193	



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